

**Notice of References Cited**

Application/Control No.

09/873,227

Applicant(s)/Patent Under  
Reexamination  
REZNIK, DANIEL

Examiner

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Art Unit

2822

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*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
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**NON-PATENT DOCUMENTS**

*		Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages)
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\*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)  
Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.